Powering a Cat Warmer Using Bi_2Te_3 Thin-Film Thermoelectric Conversion of Microprocessor Waste Heat

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I. INTRODUCTION

New thin-film materials offer potentially greater efficiencies when converting heat to electricity using the thermoelectric effect. Applied to microprocessors, this technology can mitigate a number of critical problems in one fell swoop: the dangerous amount of heat produced by laptops [14], [17], climate-change inducing electricity consumption [11], and unhappy house-cats that are insufficiently warm [1]. Figure 2 depicts an apparatus that addresses these three problems comprehensively, by extracting waste heat from a high-end microprocessor, converting the heat to electricity using thin-film technology, and using the resultant current to power a portable cat warmer.

The thermoelectric effect discovered by Seebeck in 1822 can be utilized to convert heat differentials into electric voltage [6]. When one end of metal is heated, it behaves like a battery, as the thermal gradient causes the electrons to diffuse and the phonons¹ to vibrate. The vibrating phonons preferentially allow some electrons to diffuse towards one end, creating a difference in potential. The efficiency of thermoelectric generators (TEG) is generally low (2-4%), but recent advances in nanotechnology indicate that newer materials can improve the efficiency at least two-fold [5]. TEG made out of new nanomaterials can benefit microprocessors; even a 6W recovery from a 100W processor can be enough to drive the processor cooling fan, power up certain microarchitectural structures, or ensure that house-cats are sufficiently cozy.

II. A BRIEF AND INCOMPLETE HISTORY OF THERMOELECTRIC GENERATION

Seebeck's Discovery		Cardiac Pacemake	rs	First Hi–ZT Non–bulk Materials		BiTe Nanowire	es t	SiGe hin-film coolers
	1957	1	1980)s	20	02		
1822	322 1970s			2000	1	2004		2006
	First Waste Heat Recovery from Kerosene Lamp			irst IC enerators		Poly–Si Generators For Watches (1UW)		

Fig. 1. A Brief (and Incomplete) History of Thermoelectric Generation

¹A phonon is a fundamental quantum mechanical vibration mode of a material that is used to explain sound in solids.

Min and Rowe [10] trace (Figure 1) the first instance of thermoelectric generation from wasted heat back to 1957. The invention is credited to Ioffe et al. who used heat from kerosene lamp to power a radio. Min and Rowe also report that cardiac pacemakers powered by TEG were invented and used in the 1970s, driven by heat from decaying radio isotopes. The 1980s saw the first efforts towards IC-based TEGs [7]. These and more recent CMOS TEGs [4], [12] produce power in the order of microwatts and are used in low-power devices such as sensors or body-heat-powered wrist watches.

During the late 1990s, the ability to photograph lattice structures (through x-ray diffraction), coupled with high precision fabrication techniques for nanoscale engineering, enabled the development of newer materials that are better suited for TEG [8]. These new materials have a higher figure-of-merit (ZT) compared to traditional "bulk" manufactured devices and are usually referred to as *thin-film* devices; a Si bulk device has a ZT of around 0.04, whereas a Bi_2Te_3 thin-film device has a ZT of 2.37 at 300K [15]. These thin-film devices and self-assembled nanowires [9], [13], [18] promise excellent thermoelectric conversion ratios and have rekindled the interest in TEG. In fact, recently an on-chip thermoelectric refrigerator for cooling microprocessors was built using SiGe thin-film technology [16]. Researchers have also proposed some non IC based bulk TEG for utilizing microprocessor waste heat [2], [3]. Unlike these TEGs, thin-film TEGs can be integrated within the microprocessor.

III. THERMOELECTRIC GENERATION

The maximum efficiency of any conversion process – the Carnot efficiency – is defined by the following equation:

$$Carnot = \frac{(T_h - T_c)}{T_h} \tag{1}$$

where T_h is the temperature of the hot end and T_c is the temperature of the cold end. Assuming a 50K temperature differential, with the hot end at 350K, the maximum possible conversion efficiency is 14%. In practice, however, the efficiency depends on several material properties including the Seebeck Coefficient (α)², the thermal conductivity (ρ) and the

²The open circuit voltage induced per unit temperature difference.

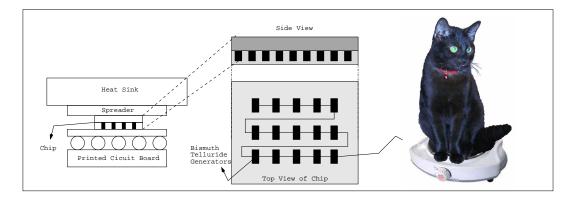


Fig. 2. A Microprocessor-Powered Bi2Te3 TEG Cat-Warmer

electrical conductivity (λ). These factors are captured with a single number–the *figure-of-merit* (*ZT*) of the material:

$$ZT = \frac{\alpha^2 T_a}{\rho \lambda} \tag{2}$$

The efficiency also depends on the generator resistance, R_g , which should be small to limit the energy lost due self-heating of the wire from the current induced in the generator (the joule heating or the I^2R_g heat loss in the generator). The low resistance requirement precludes the use of wires running in the plane of the chip, say from a hot-spot to the cooler periphery. However, thick vertical vias running down the chip layers provides a satisfactory low resistance alternative (Figure 2). The maximum power delivered by a thermoelectric system can be derived [6] to be:

$$Power = \frac{1}{R_g} \left(\frac{\alpha \times (T_h - T_c)}{\sqrt{(1 + ZT_a)} + 1} \right)^2$$
(3)

Electrical Resistivity (ρ)	$1.2 \times 10^{-5} \Omega M^{-1}$			
Seebeck Coefficient (α)	$243 \mu V K^{-1}$			
Thermal Conductivity (λ)	$0.97 \dot{W} m^{-1} K^{-1}$			
Figure of Merit: Z.T	2.37			
Temperature at hot end (T_h)	350K			
Temperature at cold end (T_c)	300K			
Average Temperature (T_a)	325K			
Silicon wafer height (L)	$5 imes 10^{-4} M$			
Via Area (A)	$1 cm^2$			
TABLE I				

TABLE OF CONSTANTS. FROM [15]

Using the constants from Venkatasubramaniam et al. [15] (summarized in Table I) in equation 3, we estimate that the maximum power that can be generated from one generator is 0.5W. By chaining multiple generators in series as shown in Figure 2, it is possible to produce the 6W required to power a gentle cat warmer for those cold Texas nights.

IV. LIMITATIONS AND FUTURE DIRECTIONS

In this paper we have assumed that thin-film devices can be effectively integrated into the semiconductor manufacturing process. Thin-film devices are fabricated using molecular beam epitaxy. There is some evidence that fabrication is possible [16] but the economic feasibility of this process is unclear. Furthermore, reductions in microprocessor die sizes may decrease the number of generators that can be placed on the die and hence decrease the total power output. However, a smaller die size may produce a higher temperature gradient, enabling more efficient TEGs. In the future, these on-chip TEGs may open up new power-performance tradeoffs for architects to examine. We note, however, that even highly efficient TEG can only reclaim one billionth of the theoretical power overhead in modern processors—the theoretical energy required to execute a program is in the order of nanoJoules, measured in energy per bit flip. In the future, with new architectures, execution models and materials, it should be possible to save/harvest enough power to drive a cat shaver, a cat petter or even a robotic cat companion.

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